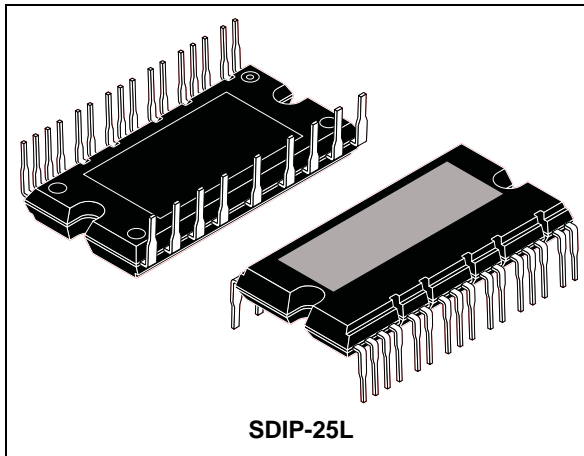


## SLLIMM™ small low-loss intelligent molded module IPM, 3-phase inverter - 30 A, 600 V short-circuit rugged IGBT

Datasheet - preliminary data



### Applications

- 3-phase inverters for motor drives
- Air conditioners

### Description

This intelligent power module provides a compact, high performance AC motor drive in a simple, rugged design. Combining ST proprietary control ICs with the most advanced short-circuit-rugged IGBT system technology, this device is ideal for 3-phase inverters in applications such as motor drives and air conditioners. SLLIMM™ is a trademark of STMicroelectronics.

### Features

- IPM 30 A, 600 V 3-phase IGBT inverter bridge including control ICs for gate driving and free-wheeling diodes
- Short-circuit rugged IGBTs
- 3.3 V, 5 V, 15 V CMOS/TTL inputs comparators with hysteresis and pull-down / pull-up resistors
- Undervoltage lockout
- Internal bootstrap diode
- Interlocking function
- Shutdown function
- DBC leading to low thermal resistance
- Isolation rating of 2500 V<sub>rms</sub>/min
- 4.7 kΩ NTC for temperature control
- UL recognized: UL1557 file E81734

**Table 1. Device summary**

Order code	Marking	Package	Packing
STGIPS30C60T-H	GIPS30C60T-H	SDIP-25L	Tube

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# 1 Internal block diagram and pin configuration

Figure 1. Internal block diagram

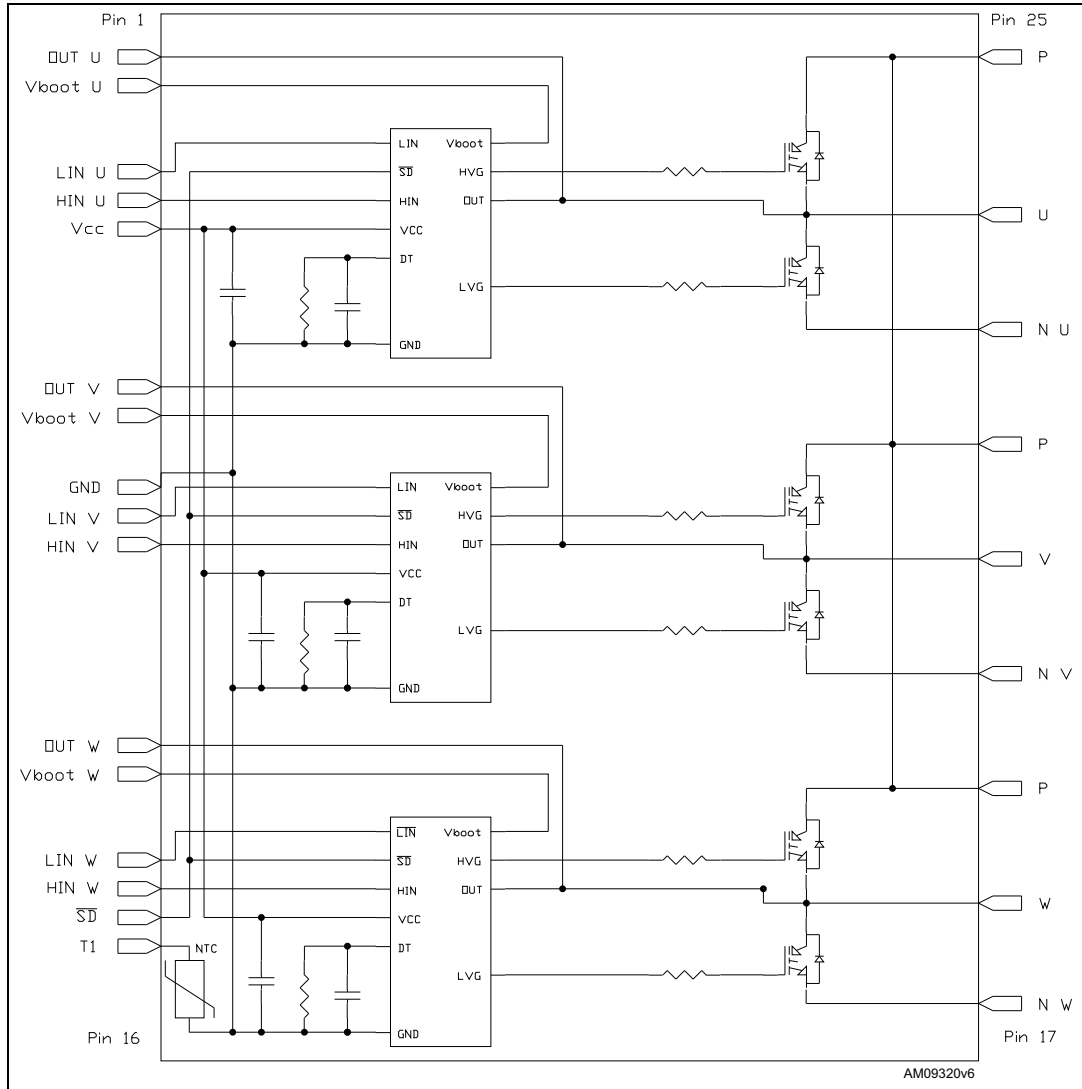
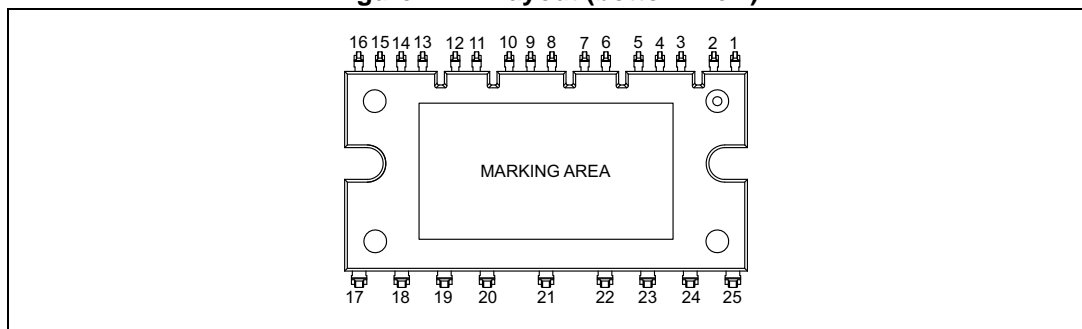


Table 2. Pin description

Pin n°	Symbol	Description
1	OUT <sub>U</sub>	High-side reference output for U phase
2	V <sub>bootU</sub>	Bootstrap voltage for U phase
3	LIN <sub>U</sub>	Low-side logic input for U phase
4	HIN <sub>U</sub>	High-side logic input for U phase
5	V <sub>CC</sub>	Low voltage power supply
6	OUT <sub>V</sub>	High-side reference output for V phase
7	V <sub>boot V</sub>	Bootstrap voltage for V phase
8	GND	Ground
9	LIN <sub>V</sub>	Low-side logic input for V phase
10	HIN <sub>V</sub>	High-side logic input for V phase
11	OUT <sub>W</sub>	High-side reference output for W phase
12	V <sub>boot W</sub>	Bootstrap voltage for W phase
13	LIN <sub>W</sub>	Low-side logic input for W phase
14	HIN <sub>W</sub>	High-side logic input for W phase
15	$\overline{SD}$	Shutdown logic input (active low)
16	T1	NTC thermistor terminal
17	N <sub>W</sub>	Negative DC input for W phase
18	W	W phase output
19	P	Positive DC input
20	N <sub>V</sub>	Negative DC input for V phase
21	V	V phase output
22	P	Positive DC input
23	N <sub>U</sub>	Negative DC input for U phase
24	U	U phase output
25	P	Positive DC input

Figure 2. Pin layout (bottom view)



## 2 Electrical ratings

### 2.1 Absolute maximum ratings

**Table 3. Inverter part**

Symbol	Parameter	Value	Unit
$V_{PN}$	Supply voltage applied between P - $N_U$ , $N_V$ , $N_W$	450	V
$V_{PN(surge)}$	Supply voltage (surge) applied between P - $N_U$ , $N_V$ , $N_W$	500	V
$V_{CES}$	Each IGBT collector emitter voltage ( $V_{IN}^{(1)} = 0$ )	600	V
$\pm I_C$	Each IGBT continuous collector current at $T_C = 25^\circ\text{C}$	30	A
$\pm I_{CP}^{(2)}$	Each IGBT pulsed collector current	60	A
$P_{TOT}$	Each IGBT total dissipation at $T_C = 25^\circ\text{C}$	52	W
$t_{scw}$	Short circuit withstand time, $V_{CE} = 0.5 V_{(BR)CES}$ $T_J = 125^\circ\text{C}$ , $V_{CC} = V_{boot} = 15\text{ V}$ , $V_{IN(1)} = 0 - 5\text{ V}$	5	$\mu\text{s}$

1. Applied between  $HIN_i$ ,  $LIN_i$  and GND for  $i = U, V, W$
2. Pulse width limited by max junction temperature

**Table 4. Control part**

Symbol	Parameter	Value	Unit
$V_{OUT}$	Output voltage applied between $OUT_U$ , $OUT_V$ , $OUT_W$ - GND	$V_{boot} - 21$ to $V_{boot} + 0.3$	V
$V_{CC}$	Low voltage power supply	-0.3 to +21	V
$V_{boot}$	Bootstrap voltage applied between $V_{boot\ i} - OUT_i$ for $i = U, V, W$	-0.3 to 620	V
$V_{IN}$	Logic input voltage applied between $HIN$ , $LIN$ and GND	-0.3 to 15	V
$V_{SD}$	Open drain voltage	-0.3 to 15	V
$dV_{OUT}/dt$	Allowed output slew rate	50	V/ns

**Table 5. Total system**

Symbol	Parameter	Value	Unit
$V_{ISO}$	Isolation withstand voltage applied between each pin and heatsink plate (AC voltage, $t = 60\text{ sec.}$ )	2500	V
$T_j$	Power chips operating junction temperature	-40 to 150	$^\circ\text{C}$
$T_C$	Module case operation temperature	-40 to 125	$^\circ\text{C}$

## 2.2 Thermal data

Table 6. Thermal data

Symbol	Parameter	Value	Unit
$R_{thJC}$	Thermal resistance junction-case single IGBT	2.4	°C/W
	Thermal resistance junction-case single diode	5	°C/W

Figure 3. Maximum  $I_{C(RMS)}$  current vs. switching frequency (1)

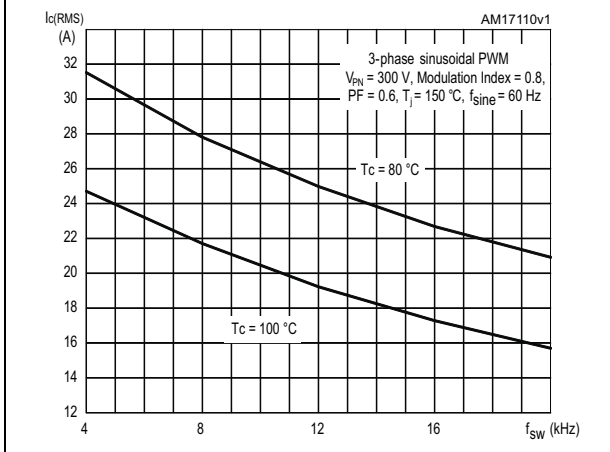
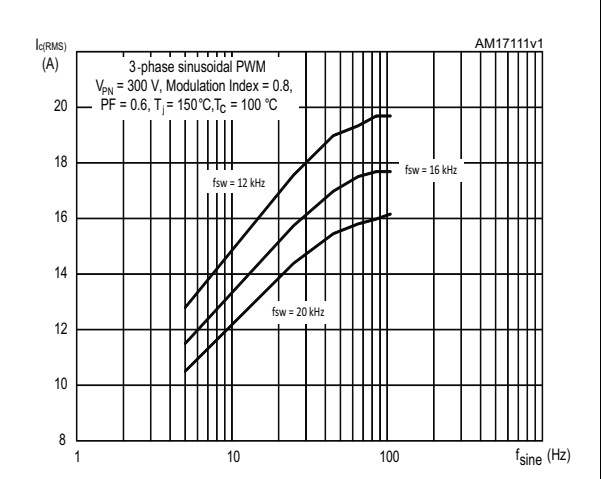


Figure 4. Maximum  $I_{C(RMS)}$  current vs.  $f_{sine}$  (1)



1. Simulated curves refer to typical IGBT parameters and maximum  $R_{thj-c}$ .

### 3 Electrical characteristics

$T_J = 25\text{ °C}$  unless otherwise specified.

**Table 7. Inverter part**

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{CC} = V_{boot} = 15\text{ V}$ , $V_{IN}^{(1)} = 0 \div 5\text{ V}$ , $I_C = 30\text{ A}$	-	1.9	2.4	V
		$V_{CC} = V_{boot} = 15\text{ V}$ , $V_{IN}^{(1)} = 0 \div 5\text{ V}$ , $I_C = 30\text{ A}$ , $T_J = 125\text{ °C}$	-	2.2		
$I_{CES}$	Collector-cut off current ( $V_{IN}^{(1)} = 0$ "logic state")	$V_{CE} = 550\text{ V}$ , $V_{CC} = V_{Boot} = 15\text{ V}$	-		100	$\mu\text{A}$
$V_F$	Diode forward voltage	$V_{IN}^{(1)} = 0$ "logic state", $I_C = 30\text{ A}$	-		2.35	V
<b>Inductive load switching time and energy</b>						
$t_{on}$	Turn-on time	$V_{PN} = 300\text{ V}$ , $V_{CC} = V_{boot} = 15\text{ V}$ , $V_{IN}^{(1)} = 0 \div 5\text{ V}$ , $I_C = 30\text{ A}$ (see <a href="#">Figure 5</a> )	-	440	-	ns
$t_{c(on)}$	Crossover time (on)		-	190	-	
$t_{off}$	Turn-off time		-	780	-	
$t_{c(off)}$	Crossover time (off)		-	135	-	
$t_{rr}$	Reverse recovery time		-	505	-	$\mu\text{J}$
$E_{on}$	Turn-on switching losses		-	870	-	
$E_{off}$	Turn-off switching losses		-	740	-	

1. Applied between  $HIN_i$ ,  $LIN_i$  and GND for  $i = U, V, W$ .

*Note:*  $t_{ON}$  and  $t_{OFF}$  include the propagation delay time of the internal drive.  $t_{C(ON)}$  and  $t_{C(OFF)}$  are the switching time of IGBT itself under the internally given gate driving condition.

Figure 5. Switching time test circuit

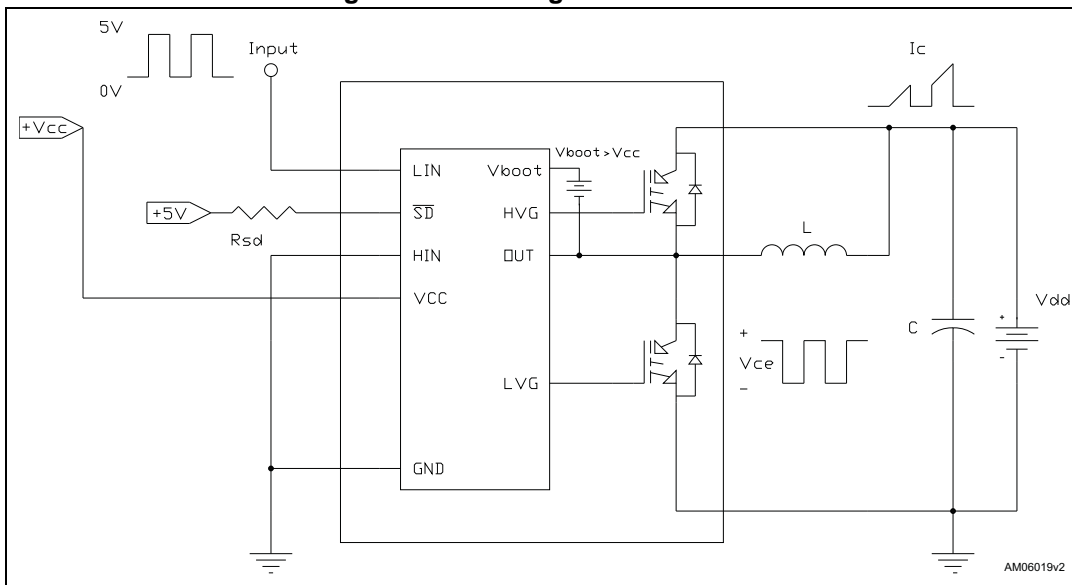


Figure 6. Switching time definition

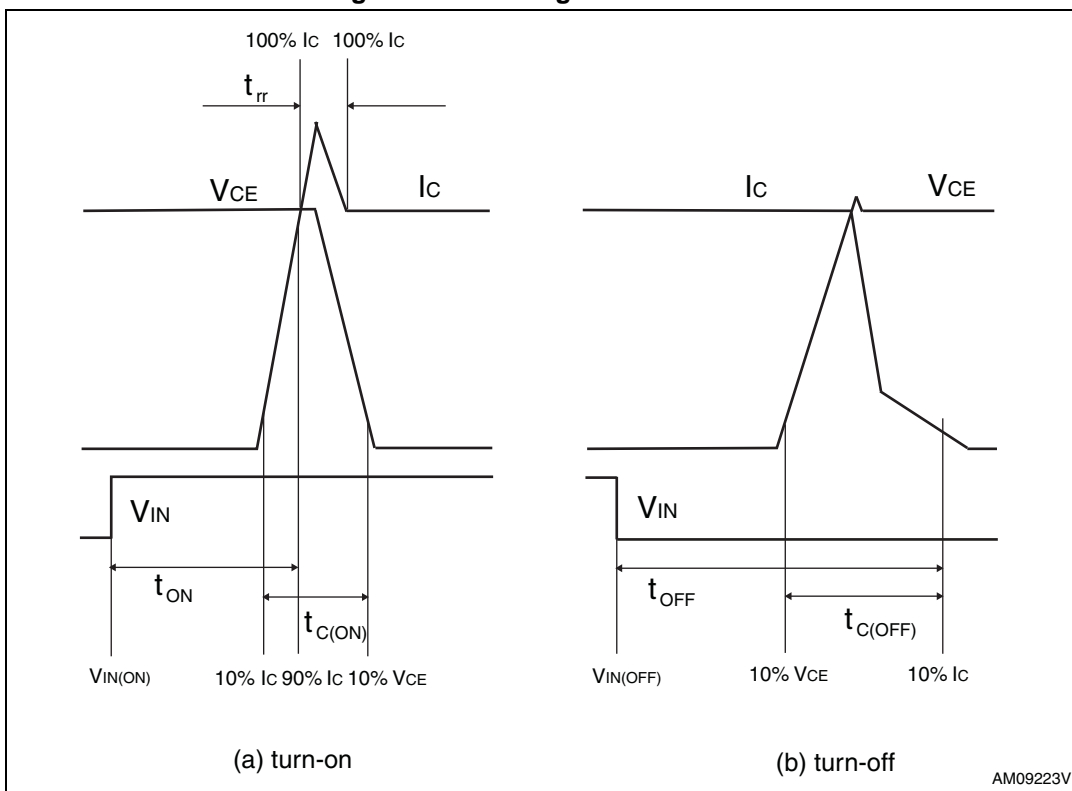


Figure 4 "Switching time definition" refers to HIN, LIN inputs (active high).



### 3.1 Control part

**Table 8. Low voltage power supply ( $V_{CC} = 15\text{ V}$  unless otherwise specified)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{CC\_hys}$	$V_{CC}$ UV hysteresis		1.2	1.5	1.8	V
$V_{CC\_thON}$	$V_{CC}$ UV turn ON threshold		11.5	12	12.5	V
$V_{CC\_thOFF}$	$V_{CC}$ UV turn OFF threshold		10	10.5	11	V
$I_{qccu}$	Undervoltage quiescent supply current	$V_{CC} = 10\text{ V}$ $\overline{SD} = 5\text{ V}$ ; LIN = 0; HIN = 0			450	$\mu\text{A}$
$I_{qcc}$	Quiescent current	$V_{CC} = 15\text{ V}$ $\overline{SD} = 5\text{ V}$ ; LIN = 0; HIN = 0			3.5	mA

**Table 9. Bootstrapped voltage ( $V_{CC} = 15\text{ V}$  unless otherwise specified)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{BS\_hys}$	$V_{BS}$ UV hysteresis		1.2	1.5	1.8	V
$V_{BS\_thON}$	$V_{BS}$ UV turn ON threshold		11.1	11.5	12.1	V
$V_{BS\_thOFF}$	$V_{BS}$ UV turn OFF threshold		9.8	10	10.6	V
$I_{QBSU}$	Undervoltage $V_{BS}$ quiescent current	$V_{BS} < 9\text{ V}$ $\overline{SD} = 5\text{ V}$ ; LIN = 0; HIN = 5 V		70	110	$\mu\text{A}$
$I_{QBS}$	$V_{BS}$ quiescent current	$V_{BS} = 15\text{ V}$ $\overline{SD} = 5\text{ V}$ ; LIN = 0; HIN = 5 V		200	300	$\mu\text{A}$
$R_{DS(on)}$	Bootstrap driver on resistance	LIN = 5 V; HIN = 0 V		120		$\Omega$

**Table 10. Logic inputs ( $V_{CC} = 15\text{ V}$  unless otherwise specified)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{il}$	Low logic level voltage		0.8		1.1	V
$V_{ih}$	High logic level voltage		1.9		2.25	V
$I_{HINh}$	HIN logic "1" input bias current	HIN = 15 V	20	40	100	$\mu\text{A}$
$I_{HINi}$	HIN logic "0" input bias current	HIN = 0 V			1	$\mu\text{A}$
$I_{LINh}$	LIN logic "1" input bias current	LIN = 15 V	20	40	100	$\mu\text{A}$
$I_{LINi}$	LIN logic "0" input bias current	LIN = 0 V			1	$\mu\text{A}$
$I_{SDh}$	$\overline{SD}$ logic "0" input bias current	$\overline{SD} = 15\text{ V}$	30	120	300	$\mu\text{A}$
$I_{SDi}$	$\overline{SD}$ logic "1" input bias current	$\overline{SD} = 0\text{ V}$			3	$\mu\text{A}$
Dt	Dead time	see <a href="#">Figure 9</a> and <a href="#">Table 14</a>		1.2		$\mu\text{s}$

Table 11. Shut down characteristics ( $V_{CC} = 15\text{ V}$  unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{sd}$	Shut down to high / low side driver propagation delay	$V_{OUT} = 0$ , $V_{boot} = V_{CC}$ , $V_{IN} = 0$ to $3.3\text{ V}$	50	125	200	ns

Table 12. Truth table

Condition	Logic input ( $V_I$ )			Output	
	$\overline{SD}$	LIN	HIN	LVG	HVG
Shutdown enable half-bridge tri-state	L	X	X	L	L
Interlocking half-bridge tri-state	H	H	H	L	L
0 "logic state" half-bridge tri-state	H	L	L	L	L
1 "logic state" low side direct driving	H	H	L	H	L
1 "logic state" high side direct driving	H	L	H	L	H

Note: X: don't care

3.1.1 NTC thermistor

Table 13. NTC thermistor

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit.
R <sub>25</sub>	Resistance	T = 25°C		4.7		kΩ
R <sub>125</sub>	Resistance	T = 125°C		160		Ω
B	B-constant	T = 25°C to 85°C		3950		K
T	Operating temperature		-40		150	°C

Equation 1: resistance variation vs. temperature

$$R(T) = R_{25} \cdot e^{B \left( \frac{1}{T} - \frac{1}{298} \right)}$$

Where T are temperatures in Kelvins

Figure 7. NTC resistance vs. temperature

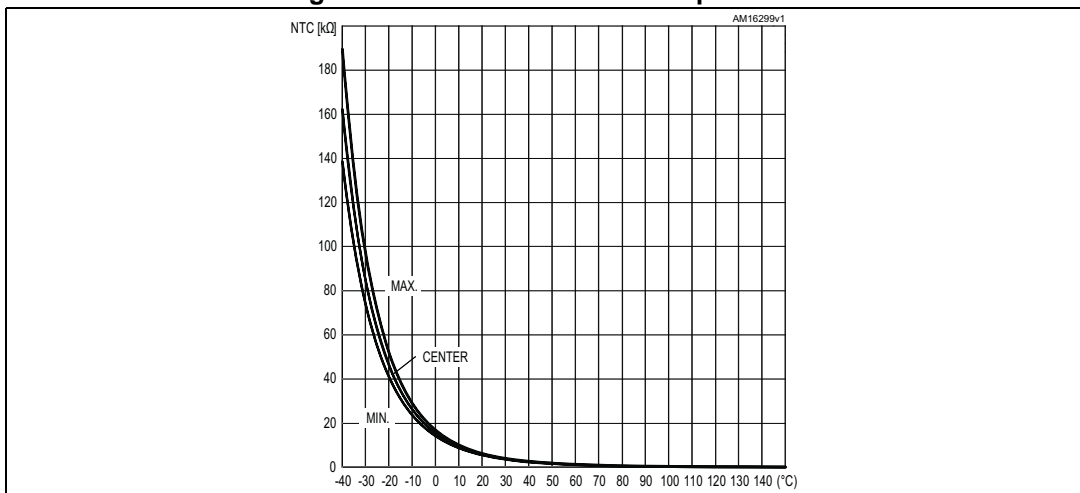
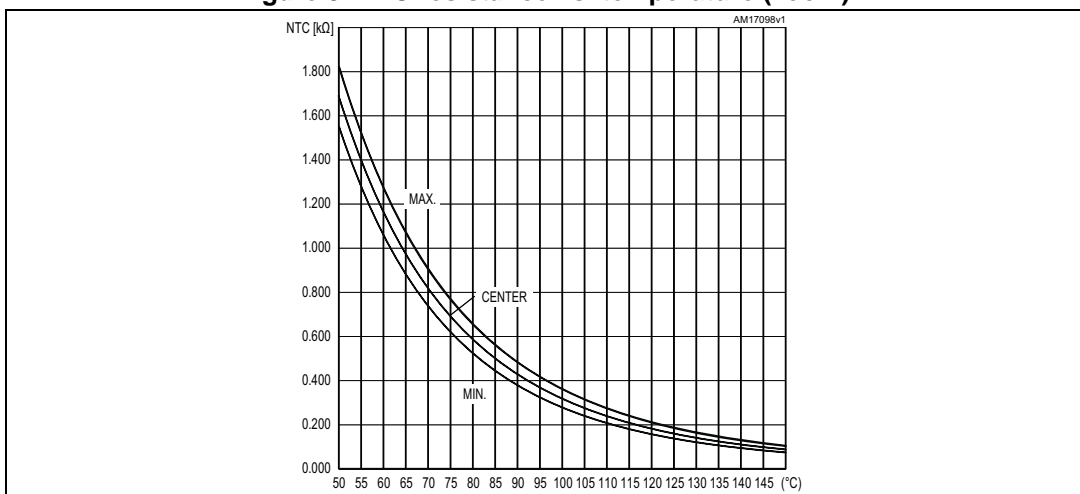
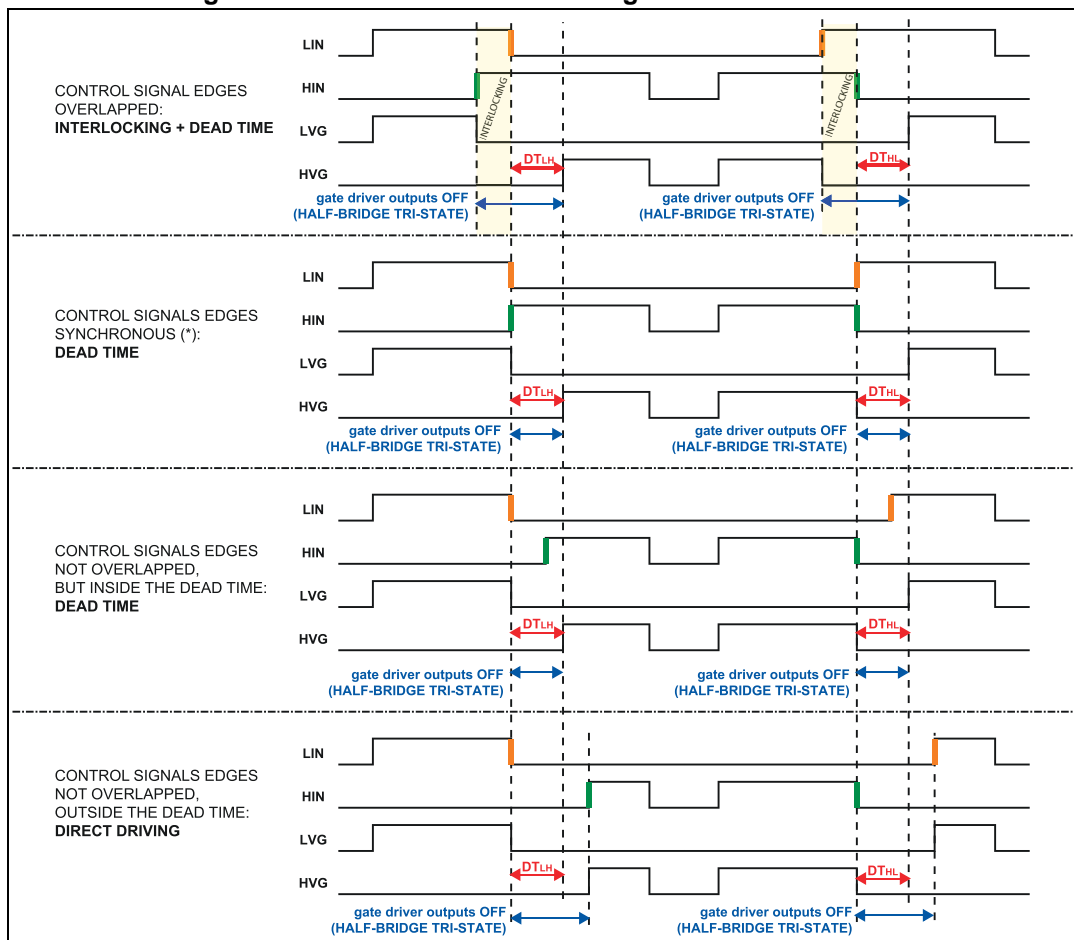


Figure 8. NTC resistance vs. temperature (zoom)



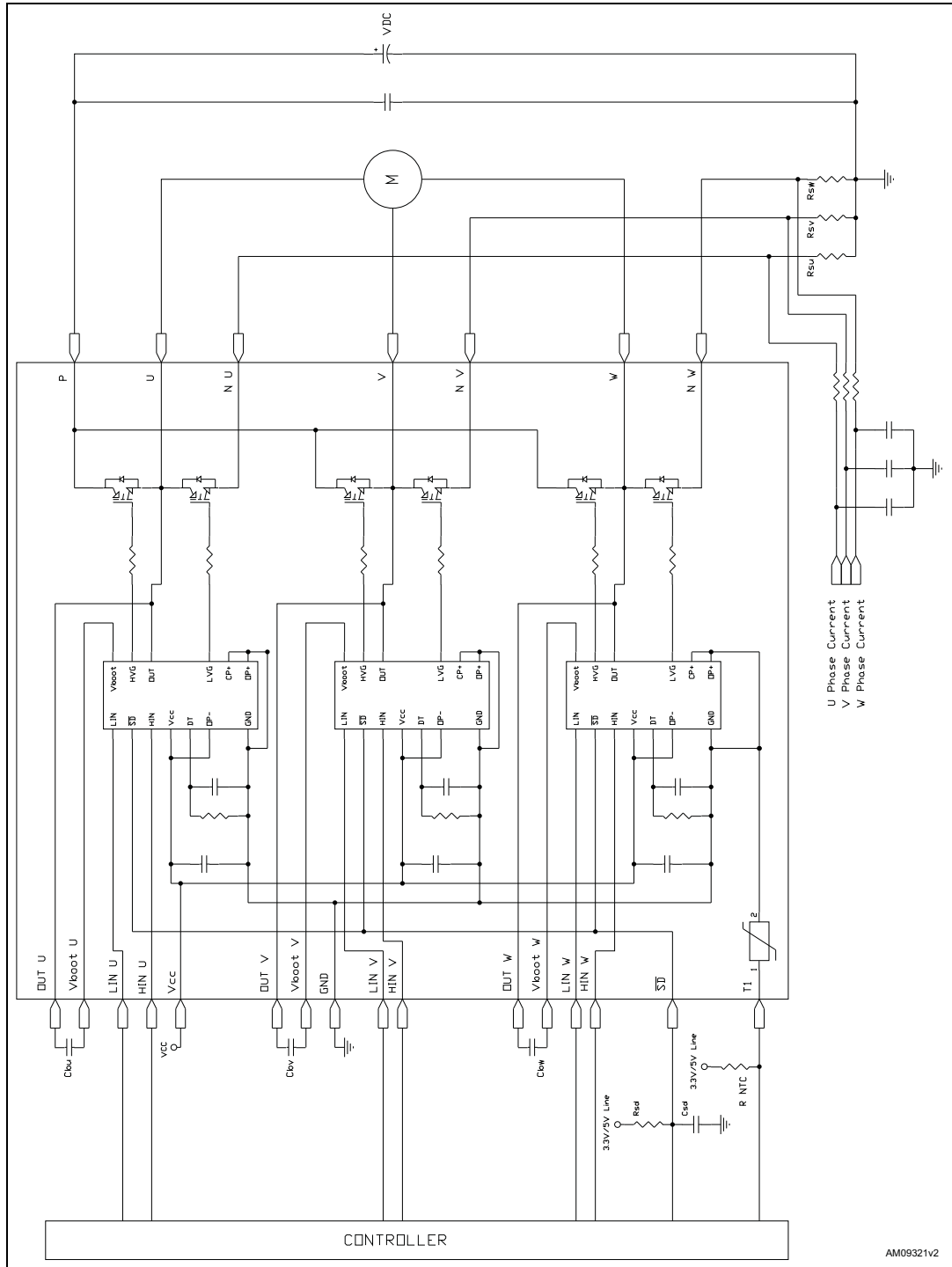
### 3.2 Waveform definitions

Figure 9. Dead time and interlocking waveform definitions



# 4 Applications information

Figure 10. Typical application circuit



### 4.1 Recommendations

- Input signals HIN, LIN are active high logic. A 375 kΩ (typ.) pull down resistor is built-in for each input. If an external RC filter is used, for noise immunity, pay attention to the variation of the input signal level.
- To prevent the input signals oscillation, the wiring of each input should be as short as possible.
- By integrating an application specific type HVIC inside the module, direct coupling to MCU terminals without any opto-coupler is possible.
- Each capacitor should be located as nearby the pins of IPM as possible.
- Low inductance shunt resistors should be used for phase leg current sensing.
- Electrolytic bus capacitors should be mounted as close to the module bus terminals as possible. Additional high frequency ceramic capacitor mounted close to the module pins will further improve performance.
- The  $\overline{SD}$  signal should be pulled up to 5 V / 3.3 V with an external resistor.

**Table 14. Recommended operating conditions**

Symbol	Parameter	Conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{PN}$	Supply Voltage	Applied between P-Nu,Nv,Nw		300	400	V
$V_{CC}$	Control supply voltage	Applied between $V_{CC}$ -GND	13.5	15	18	V
$V_{BS}$	High side bias voltage	Applied between $V_{BOOTi}$ - $OUT_i$ for $i=U,V,W$	13		18	V
$t_{dead}$	Blanking time to prevent Arm-short	For each input signal	1.5			μs
$f_{PWM}$	PWM input signal	-40°C < $T_c$ < 100°C -40°C < $T_j$ < 125°C			20	kHz
$T_c$	Case operation temperature				100	°C

Note: For further details refer to AN3338.

## 5 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

Please refer to dedicated technical note TN0107 for mounting instructions.

### 5.1 SDIP-25L package information

Figure 11. SDIP-25L package outline

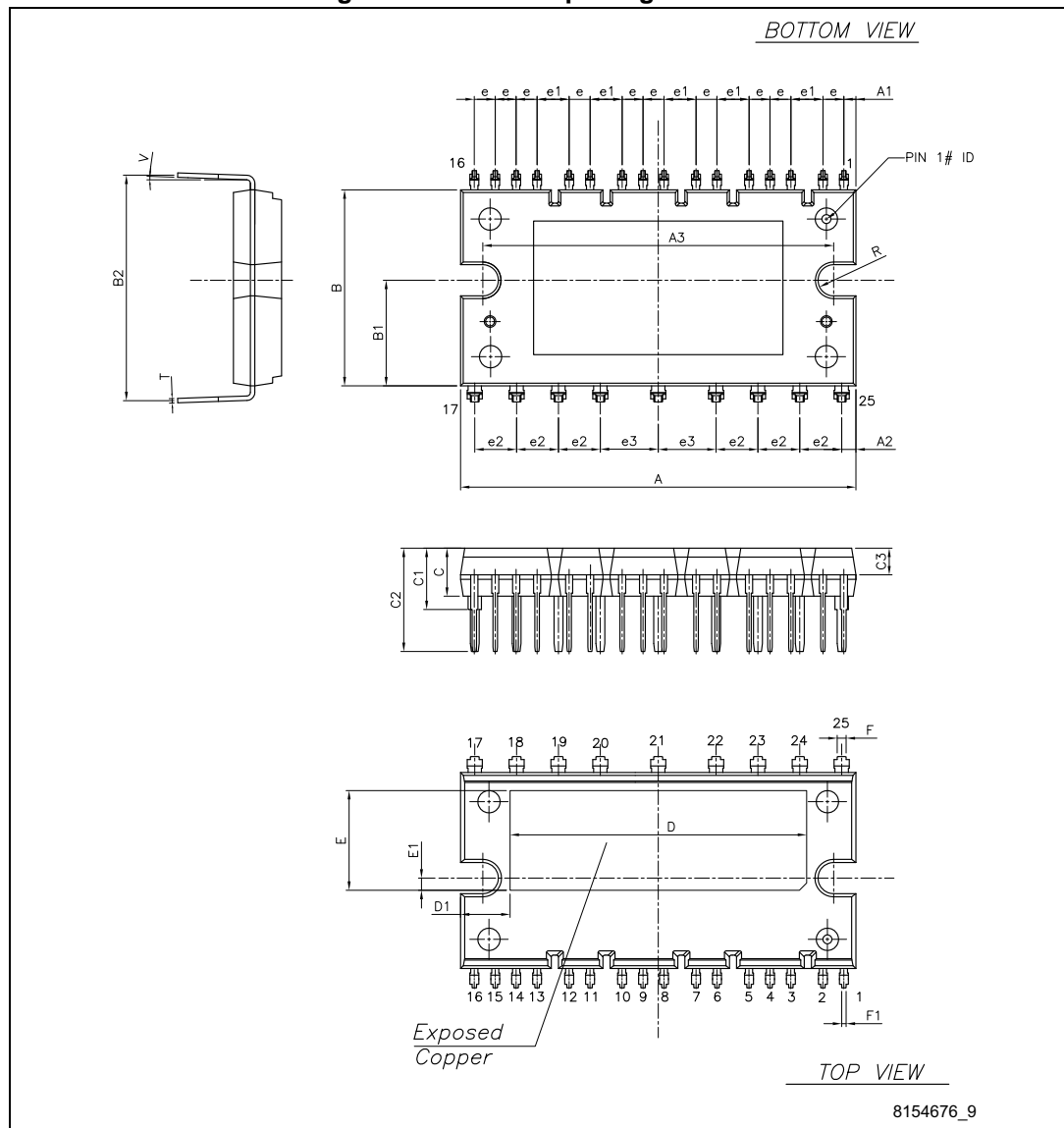


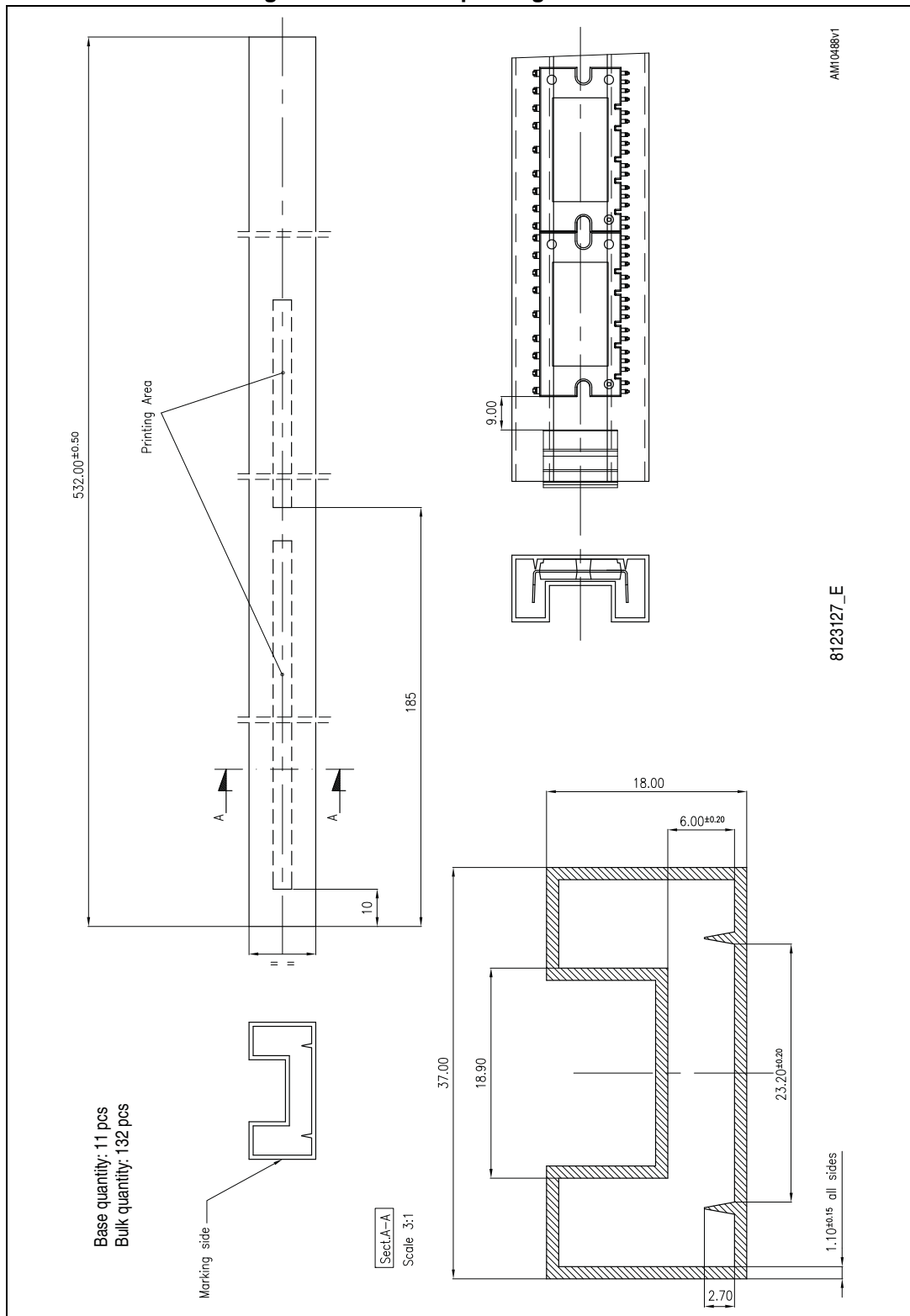
Table 15. SDIP-25L mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	43.90	44.40	44.90
A1	1.15	1.35	1.55
A2	1.40	1.60	1.80
A3	38.90	39.40	39.90
B	21.50	22.00	22.50
B1	11.25	11.85	12.45
B2	24.83	25.23	25.63
C	5.00	5.40	6.00
C1	6.50	7.00	7.50
C2	11.20	11.70	12.20
C3	2.90	3.00	3.10
e	2.15	2.35	2.55
e1	3.40	3.60	3.80
e2	4.50	4.70	4.90
e3	6.30	6.50	6.70
D		33.30	
D1		5.55	
E		11.20	
E1		1.40	
F	0.85	1.00	1.15
F1	0.35	0.50	0.65
R	1.55	1.75	1.95
T	0.45	0.55	0.65
V	0°		6°



## 5.2 Packing information

Figure 12. SDIP-25L packing information



## 6 Revision history

**Table 16. Document revision history**

Date	Revision	Changes
25-Nov-2013	1	Initial release.
14-May-2014	2	Updated <a href="#">Table 3: Inverter part</a> , <a href="#">Table 6: Thermal data</a> , <a href="#">Table 7: Inverter part</a> and <a href="#">Section 5.2: Packing information</a> . Minor text changes.
10-Apr-2015	3	Minor text edits throughout document Updated <a href="#">Figure 2: Pin layout (bottom view)</a> Updated <a href="#">Section 5: Package information</a>

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